Silicon Carbide Schottky Diode

650 V, 8 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

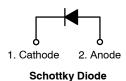
Applications

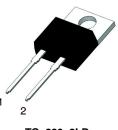
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



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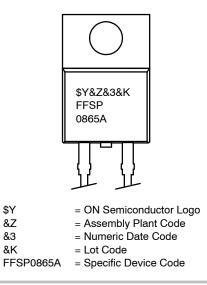
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TO-220-2LD CASE 340BB

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

| Symbol | Parameter | Value | Unit | |
|-----------------------------------|---------------------------------------------------------------|------------------------------------------|-------------|----|
| V _{RRM} | Peak Repetitive Reverse Voltage | 650 | V | |
| E _{AS} | Single Pulse Avalanche Energy (Note 1) | 49 | mJ | |
| ١ _F | Continuous Rectified Forward Current @ T _C < 155°C | | 8 | А |
| | Continuous Rectified Forward Current @ $T_C < T_C$ | 13 | 1 | |
| I _{F, Max} | Non-Repetitive Peak Forward Surge Current | T _C = 25°C, 10 μs | 750 | А |
| | | T _C = 150°C, 10 μs | 730 | А |
| I _{F,SM} | Non-Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 49 | А |
| I _{F,RM} | Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 34 | А |
| Ptot | Power Dissipation | $T_{\rm C} = 25^{\circ}{\rm C}$ | 98 | W |
| | | T _C = 150°C | 16 | W |
| T _J , T _{STG} | Operating and Storage Temperature Range | | –55 to +175 | °C |

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 49 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 14 A, V = 50 V.

THERMAL CHARACTERISTICS

| I | Symbol | Parameter | Value | Unit |
|---|-----------------|-------------------------------------------|-------|------|
| | $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max | 1.53 | °C/W |

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Тур | Max | Unit |
|----------------|-------------------------|--------------------------------------------------------------|-----|------|------|------|
| V _F | Forward Voltage | $I_{F} = 8 \text{ A}, T_{C} = 25^{\circ}\text{C}$ | - | 1.50 | 1.75 | V |
| | | I _F = 8 A, T _C = 125°C | - | 1.6 | 2.0 | |
| | | I _F = 8 A, T _C = 175°C | - | 1.72 | 2.40 | |
| Ι _R | Reverse Current | $V_{R} = 650 \text{ V}, \text{ T}_{C} = 25^{\circ}\text{C}$ | - | - | 200 | μΑ |
| | | $V_{R} = 650 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$ | - | - | 400 | |
| | | $V_{R} = 650 \text{ V}, \text{ T}_{C} = 175^{\circ}\text{C}$ | - | - | 600 | |
| Q _C | Total Capacitive Charge | V = 400 V | - | 27 | - | nC |
| С | Total Capacitance | V _R = 1 V, f = 100 kHz | - | 463 | - | pF |
| | | V _R = 200 V, f = 100 kHz | - | 48 | - | |
| | | V _R = 400 V, f = 100 kHz | - | 38 | - | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

| Part Number | Top Marking | Package | Packing Method | Quantity |
|-------------|-------------|----------------------------------------|----------------|----------|
| FFSP0865A | FFSP0865A | TO-220-2LD (Pb-Free / Halogen Free) | Tube | 50 Units |

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

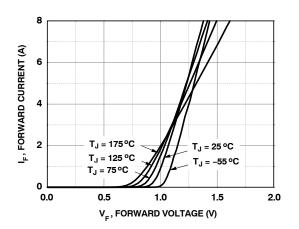


Figure 1. Forward Characteristics

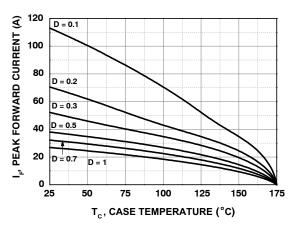


Figure 3. Current Derating

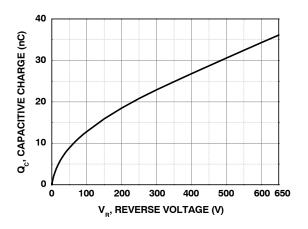


Figure 5. Capacitive Charge vs. Reverse Voltage

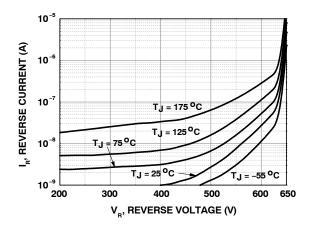


Figure 2. Reverse Characteristics

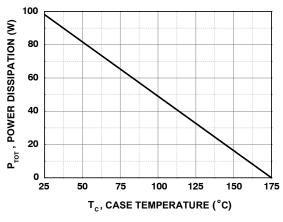


Figure 4. Power Derating

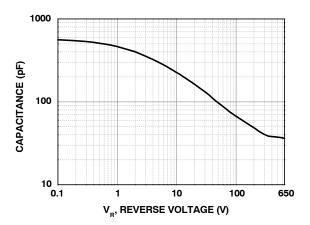


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

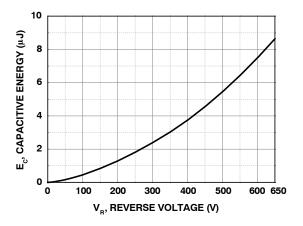


Figure 7. Capacitance Stored Energy

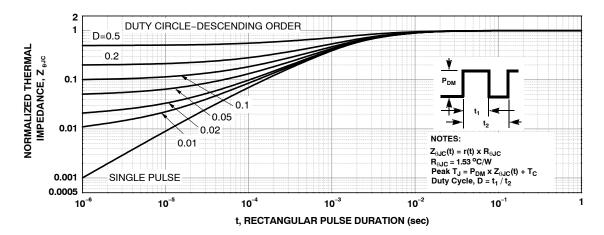


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

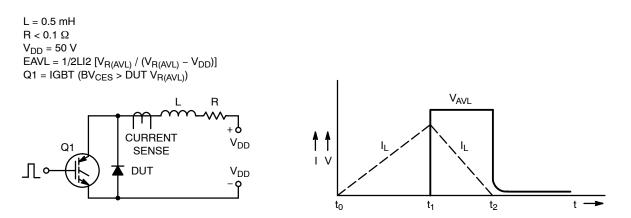
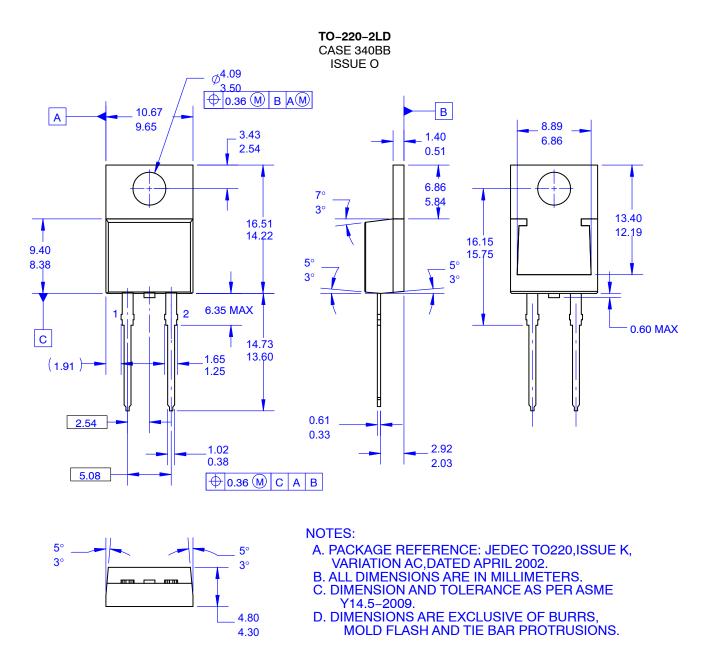


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

PACKAGE DIMENSIONS



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